



Substitute for Form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: July 10, 2006 <i>(use as many sheets as necessary)</i>		Complete if Known	
		Application Number	10/826,007
		Filing Date	04/16/2004
		First Named Inventor	Hongxing TANG
		Group Art Unit	2855
		Examiner Name	George P. Bonanto
		Attorney Docket Number	049411-0268
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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	B1	2002/0175408	A1	MAJUMDAR et al.	11/28/2002	
	B2	2003/0203531	A1	SHCHUKIN et al.	10/30/2003	
	B3	2005/0109925	A1	EL RIFAI et al.	05/2005	
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U.S. PATENT APPLICATION DOCUMENTS					
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FOREIGN PATENT DOCUMENTS						
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		Office ³	Number ⁴	Kind Code ⁵ (if known)		
MN	B14	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003
MN	B15	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003
MN	B16	WO	2004/041998	A2	California Inst. of Tech.	05/21/2004

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MN	B17	MELOSH et al., "Ultrahigh-Density Nanowire Lattices and Circuits," Science, April 4, 2003, vol. 300, pp. 112-115.	

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MN	B32	DEHE et al., "A piezoresistive GaAs pressure sensor with GaAs/AlGaAs membrane technology," J. Micromech. Microeng., 1995, vol. 5, pp. 139-142.	
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